

## **IN THE CLAIMS**

This listing of claims replaces all prior listings:

1-26 (Cancelled).

27. (Currently Amended) A solid-state image sensor comprising ~~[[:]]~~ unit pixels, each unit pixel having:

- a photoelectric conversion element for converting incident light into a electric signal charge and then storing the signal charge obtained through such photoelectric conversion;
- an amplifying element ~~for amplifying~~ effective to amplify the signal charge stored in said photoelectric conversion element into an electric signal; and
- a reset element ~~for resetting~~ effective to reset said signal charge, ~~said reset element being a depletion transistor,~~

wherein,

said reset element is a depletion mode transistor, and

the reset gate of said depletion mode transistor is a transverse overflow barrier.